SQSA82CENW

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Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY 80 V_{DS} (V) $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$ 0.0460 $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5$ V 0.0700 12 $I_D(A)$ Configuration Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

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COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK 1212-8W
Lead (Pb)-free and halogen-free	SQSA82CENW

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	80	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	T _C = 25 °C ^a	1	12		
Continuous drain current	T _C = 125 °C	I _D	9.68		
Continuous source current (diode conduction) a		۱ _S	12	А	
Pulsed drain current ^b		I _{DM}	35		
Single pulse avalanche current		I _{AS}	13		
Single pulse avalanche energy		E _{AS}	8.45	mJ	
Maximum power dissipation	T _C = 25 °C	D	27	W	
Maximum power dissipation	T _C = 125 °C	P _D	9	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^{d, e}			260	-0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	81	°C/W
Junction-to-case (drain)		R _{thJC}	5.5	0/10

Notes

a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 % c. When mounted on 1" square PCB (FR4 material)

See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK1212-8W package may have visible exposed Cu at the end of the lead terminals due to the singulation process. However, the leads also have plated indents on the top and bottom surfaces that promote the d. formation of a solder filet compatible with automated optical inspection methods

e. Rework conditions: manual soldering with a soldering iron is not recommended

S21-1135-Rev. A, 22-Nov-2021

1 For technical questions, contact: automostechsupport@vishay.com Document Number: 63157

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	80	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	ε V _{GS} , I _D = 250 μA	1.5	2.0	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	$V_{DS} = 80 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	Α	
		$V_{GS} = 10 V$	I _D = 3.5 A	-	0.0370	0.0460	ν nA μA	
	P	$V_{GS} = 10 V$	I _D = 3.5 A, T _J = 125 °C	-	-	0.0798		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.5 A, T _J = 175 °C	-	-	0.0971	50 μA 150 A 150 A 0460 Δ 0798 Ω 0971 Ω 0700 - - S 580 Δ 290 PF 3.60 Λ - NC - 1.47 Ω 12 Λ Ns 23 Ns 12	Ω
		V _{GS} = 4.5 V	I _D = 3 A	-	0.0495	0.0700		
Forward transconductance b	9 _{fs}	V _{DS} =	= 15 V, I _D = 3.5 A	-	14	-	S	
Dynamic ^b		1						
Input capacitance	C _{iss}			-	413	580		
Output capacitance	Coss	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	207	290	pF	
Reverse transfer capacitance	C _{rss}			-	12	17		
Total gate charge ^c	Qg			-	6.40	9.60		
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	-	1.65	-	nC	
Gate-drain charge ^c	Q _{gd}			-	0.66	-		
Gate resistance	R _g		f = 1 MHz	0.49	0.98	1.47	Ω	
Turn-on delay time ^c	t _{d(on)}			-	7	12		
Rise time ^c	t _r	V _{DD} =	= 40 V, R _L = 10 Ω	-	3	6	1	
Turn-off delay time ^c	t _{d(off)}	$ \begin{array}{c c} ss \\ ss$	23	ns				
Fall time ^c	t _f			-	3	6	1	
Source-Drain Diode Ratings and Charact	eristic ^b				•			
Pulsed current ^a	I _{SM}			-	-	35	Α	
Forward voltage	V _{SD}	I _F =	3.5 A, V _{GS} = 0 V	-	0.83	1.1	V	
Body diode reverse recovery time	t _{rr}			-	19	38	ns	
Body diode reverse recovery charge	Q _{rr}	1	-		13	26	nC	
Reverse recovery fall time	ta	- I _F = 5 A, di/dt = 100 A/μs - 13 - 11		11	-			
Reverse recovery rise time	t _b			-	8	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.16	-	Α	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

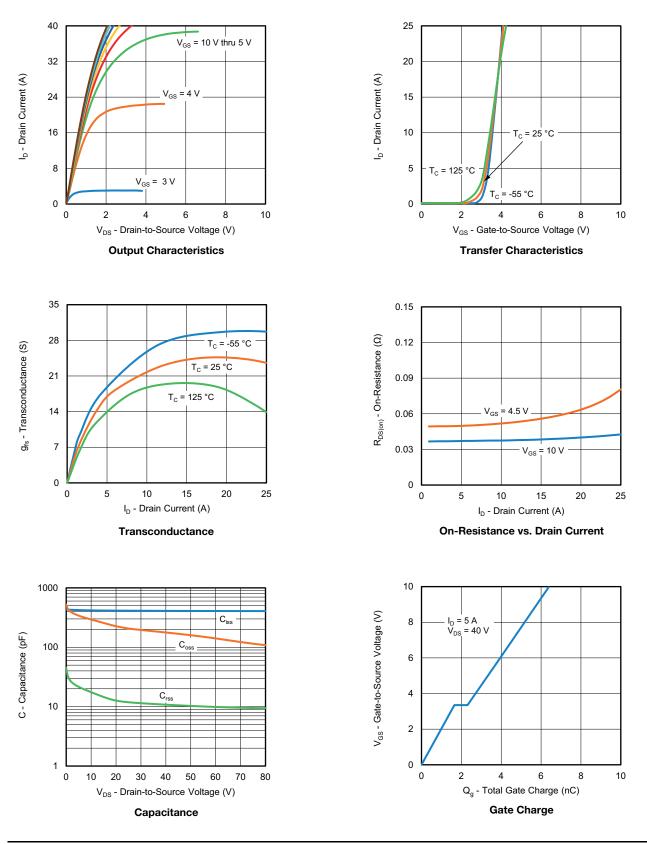
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



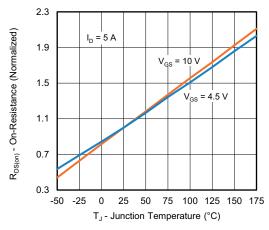
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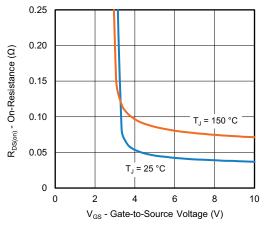
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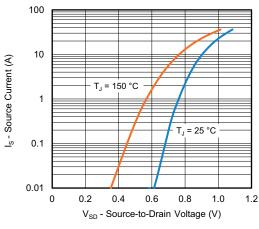
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



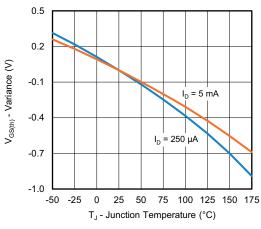
On-Resistance vs. Junction Temperature



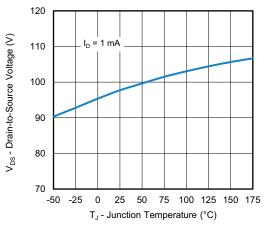
On-Resistance vs. Gate-to-Source Voltage



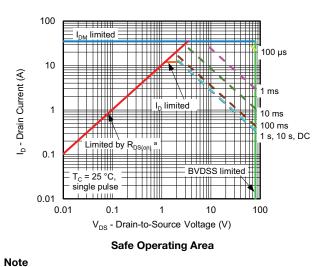
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

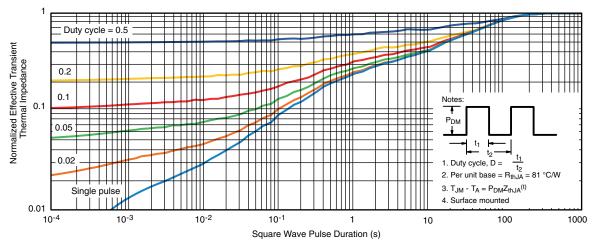
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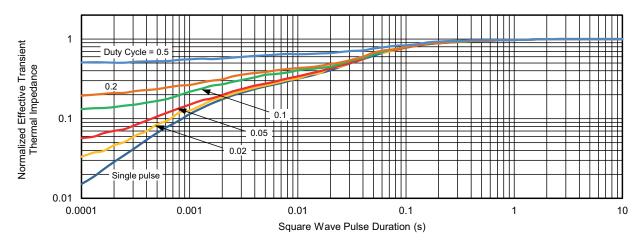




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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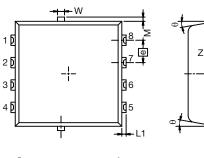
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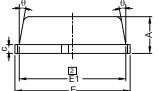


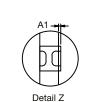
PowerPAK[®] 1212-8W Case Outline

Δ2

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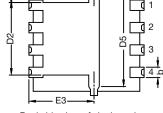




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E2

E4

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Notes
1 Inch will govern

 Dimensions exclusive of mold gate burrs
 Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0	-	0.05	0	-	0.002	
A2	0	-	0.13	0	-	0.005	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D4	0.47 typ.				0.0185 typ.		
D5	2.3 typ.		0.090 typ.				
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.34 typ.			0.013 typ.		
е		0.65 BSC.		0.026 BSC			
К		0.86 typ.		0.034 typ.			
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
N: C15-1530-R	ev. B, 16-Nov-15						

Backside view of single pad



RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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